

# 2.5V Drive Pch+SBD MOSFET

## US5U30

### ●Structure

Silicon P-channel MOSFET  
Schottky Barrier DIODE

### ●Features

- 1) The US5U30 combines Pch MOSFET with a Schottky barrier diode in a TUMT5 package.
- 2) Low on-state resistance with fast switching.
- 3) Low voltage drive(2.5V)
- 4) Built-in schottky barrier diode has low forward voltage.

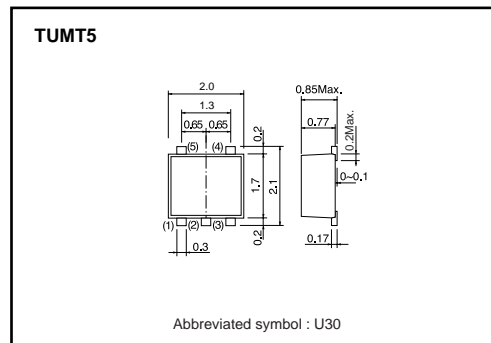
### ●Applications

Load switch, DC/DC conversion

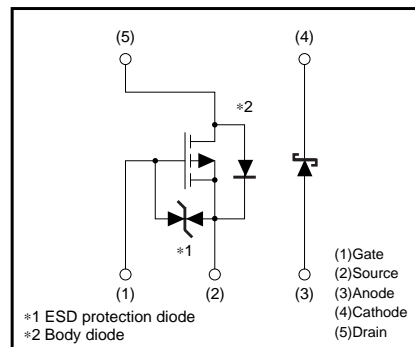
### ●Packaging specifications

Type	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
US5U30		○

### ●Dimensions (Unit : mm)



### ●Equivalent circuit



## Transistor

## ●Absolute maximum ratings (Ta=25°C)

&lt;MOSFET&gt;

Parameter	Symbol	Limits	Unit	
Drain-source voltage	V <sub>DSS</sub>	-20	V	
Gate-source voltage	V <sub>GSS</sub>	±12	V	
Drain current	Continuous	I <sub>D</sub>	±1	A
	Pulsed	I <sub>DP</sub> *1	±4	A
Source current (Body diode)	Continuous	I <sub>S</sub>	-0.4	A
	Pulsed	I <sub>SP</sub> *1	-4	A
Channel temperature	T <sub>ch</sub>	150	°C	
Power dissipation	P <sub>D</sub> *3	0.7	W / ELEMENT	

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Repetitive peak reverse voltage	V <sub>RM</sub>	30	V
Reverse voltage	V <sub>R</sub>	20	V
Forward current	I <sub>F</sub>	0.5	A
Forward current surge peak	I <sub>FSM</sub> *2	2	A
Junction temperature	T <sub>j</sub>	150	°C
Power dissipation	P <sub>D</sub> *3	0.5	W / ELEMENT

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Total power dissipation	P <sub>D</sub> *3	1.0	W / TOTAL
Range of Storage temperature	T <sub>stg</sub>	-55 to +150	°C

\*1 Pw≤10μs, Duty cycles≤1% \*2 60Hz-1cyc. \*3 Mounted on a ceramic board

## ●Electrical characteristics (Ta=25°C)

&lt;MOSFET&gt;

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I <sub>GSS</sub>	-	-	±10	μA	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	-20	-	-	V	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	-	-	-1	μA	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS(th)</sub>	-0.7	-	-2.0	V	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA
Static drain-source on-state resistance	R <sub>DS(on)</sub> *	-	280	390	mΩ	I <sub>D</sub> =-1A, V <sub>GS</sub> =-4.5V
		-	310	430	mΩ	I <sub>D</sub> =-1A, V <sub>GS</sub> =-4V
		-	570	800	mΩ	I <sub>D</sub> =-0.5A, V <sub>GS</sub> =-2.5V
Forward transfer admittance	Y <sub>fs</sub>   *	0.7	-	-	S	V <sub>DS</sub> =-10V, I <sub>D</sub> =-0.5A
Input capacitance	C <sub>iss</sub>	-	150	-	pF	V <sub>DS</sub> =-10V
Output capacitance	C <sub>oss</sub>	-	20	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	C <sub>rss</sub>	-	20	-	pF	f=1MHz
Turn-on delay time	t <sub>d(on)</sub> *	-	9	-	ns	I <sub>D</sub> =-0.5A V <sub>DD</sub> =-15V
Rise time	t <sub>r</sub> *	-	8	-	ns	V <sub>GS</sub> =-4.5V
Turn-off delay time	t <sub>d(off)</sub> *	-	25	-	ns	R <sub>L</sub> =30Ω
Fall time	t <sub>f</sub> *	-	10	-	ns	R <sub>G</sub> =10Ω
Total gate charge	Q <sub>g</sub>	-	2.1	-	nC	V <sub>DD</sub> =-15V V <sub>GS</sub> =-4.5V
Gate-source charge	Q <sub>gs</sub>	-	0.5	-	nC	I <sub>D</sub> =-1A
Gate-drain charge	Q <sub>gd</sub>	-	0.5	-	nC	R <sub>L</sub> =15Ω R <sub>G</sub> =10Ω

\* Pulsed

&lt;Body diode (source-drain)&gt;

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V <sub>SD</sub>	-	-	-1.2	V	I <sub>S</sub> =-0.4A, V <sub>GS</sub> =0V

&lt;Di&gt;

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V <sub>F</sub>	-	-	0.36	V	I <sub>F</sub> =0.1A
		-	-	0.47	V	I <sub>F</sub> =0.5A
Reverse current	I <sub>R</sub>	-	-	100	μA	V <sub>R</sub> =20V

Transistor

●Electrical characteristic curves

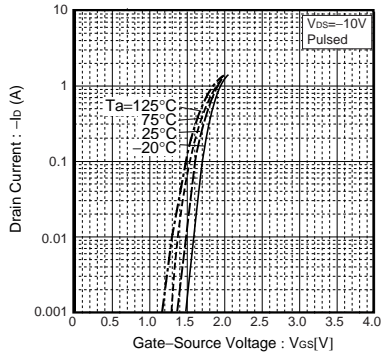


Fig.1 Typical Transfer Characteristics

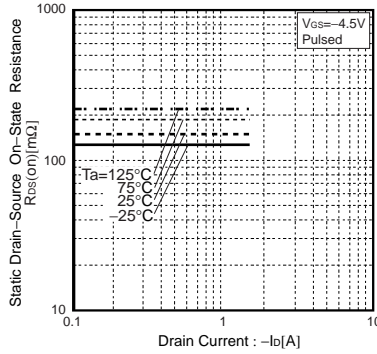


Fig.2 Static Drain-Source On-State Resistance vs. Drain Current

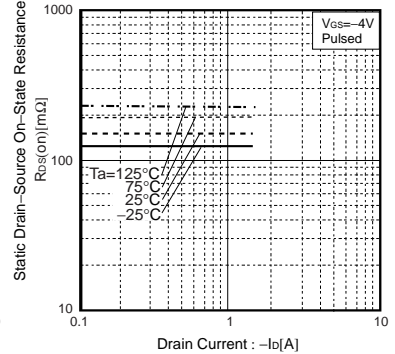


Fig.3 Static Drain-Source On-State Resistance vs. Drain Current

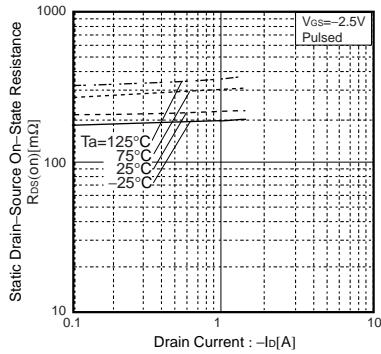


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current

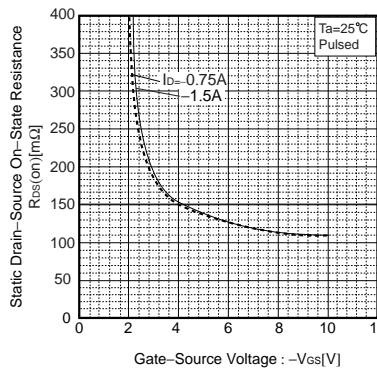


Fig.5 Static Drain-Source On-State Resistance vs. Gate-Source Voltage

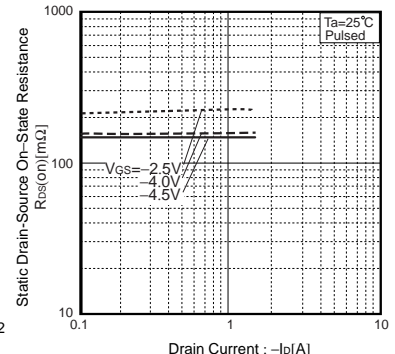


Fig.6 Static Drain-Source On-State Resistance vs. Drain Current

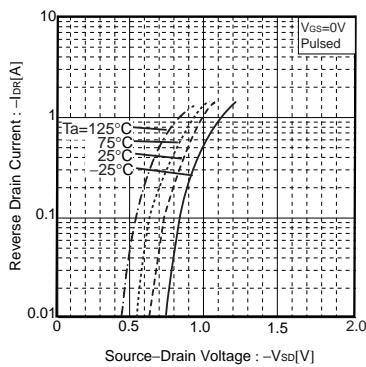


Fig.7 Reverse Drain Current vs. Source-Drain Voltage

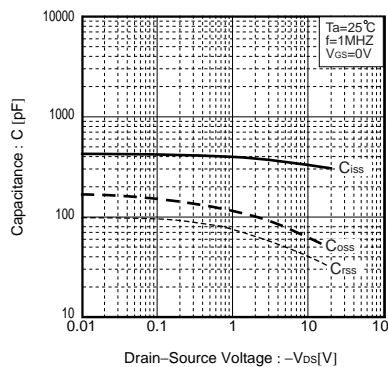


Fig.8 Typical Capacitance vs. Drain-Source Voltage

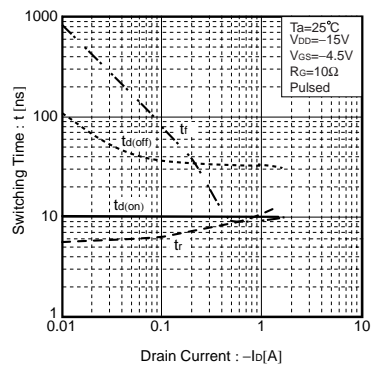


Fig.9 Switching Characteristics

Transistor

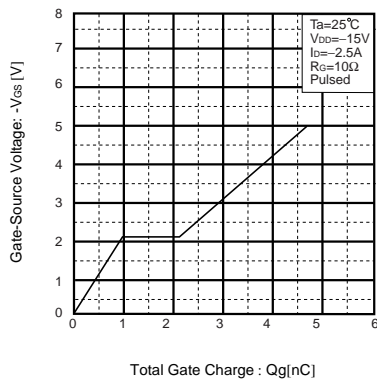


Fig.10 Dynamic Input Characteristics

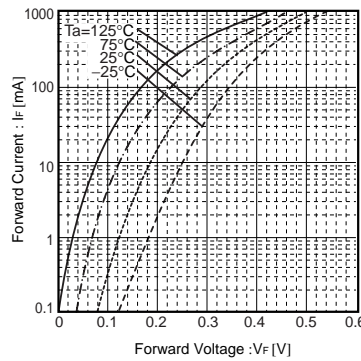


Fig.11 Forward Temperature Characteristics

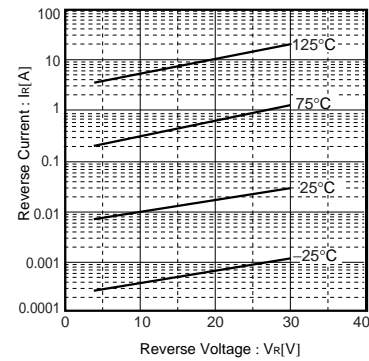


Fig.12 Reverse Temperature Characteristics

●Measurement circuits

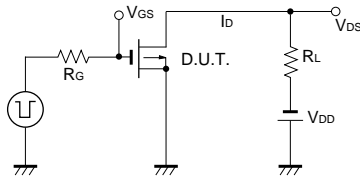


Fig.13 Switching Time Measurement Circuit

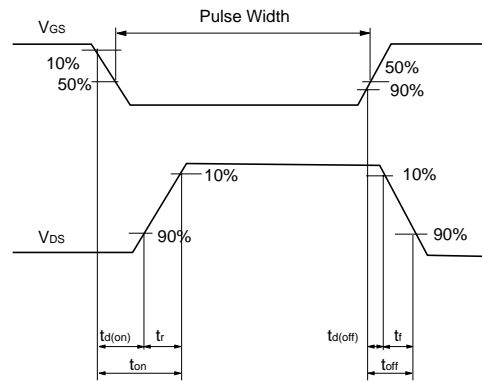


Fig.14 Switching Waveforms

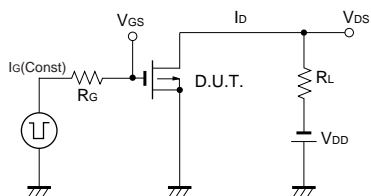


Fig.15 Gate Charge Measurement Circuit

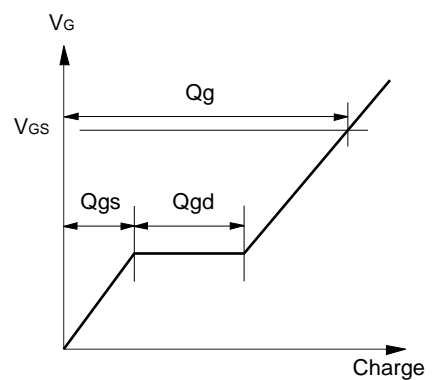


Fig.16 Gate Charge Waveforms

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